

ECE 65: Components & Circuits Lab

Lecture 12

BJT Transfer function

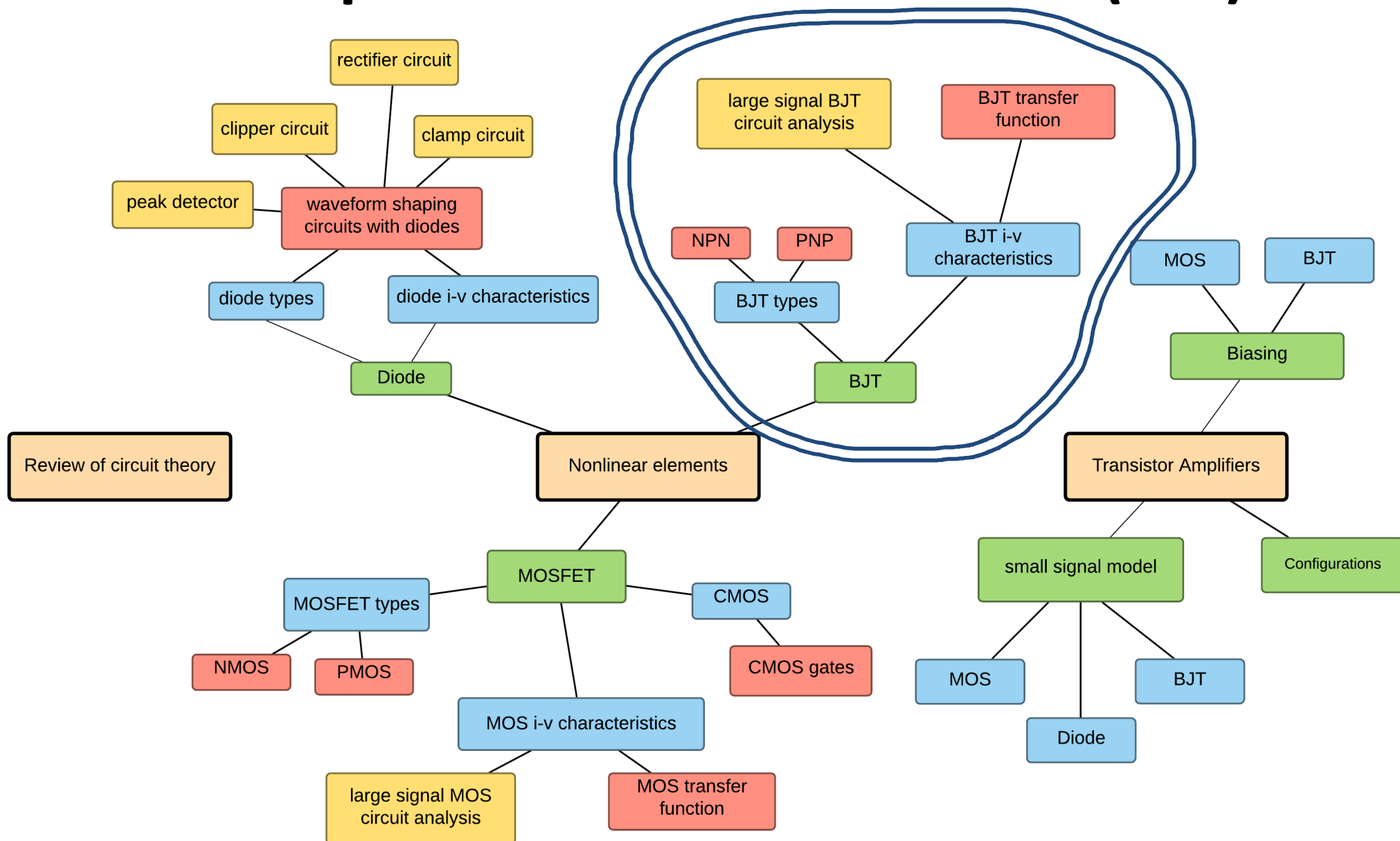
Reference notes: sections 3.2

Sedra & Smith (7th Ed): sections 6.1,6.4

Saharnaz Baghdadchi

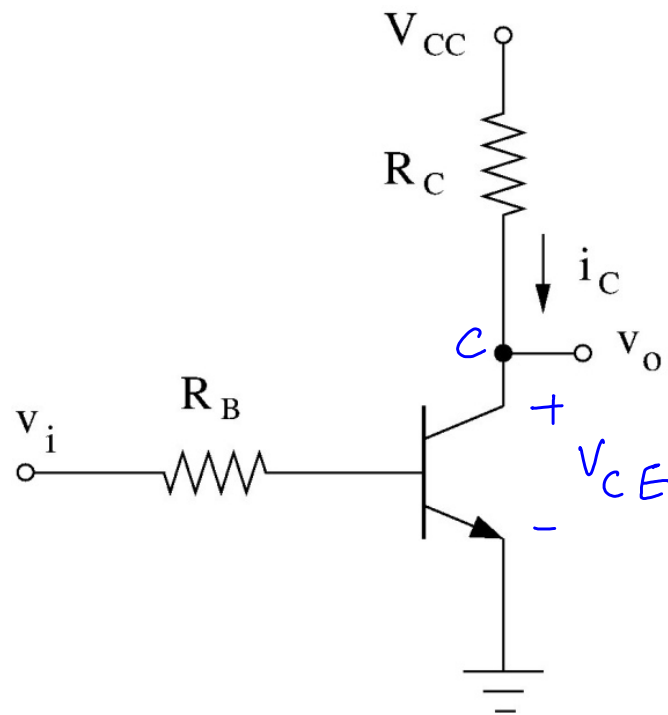
Course map

3. Bipolar Junction Transistor (BJT)



Discussion question: BJT Transfer Function

how would the output $v_o = v_{CE}$ change in terms of v_i ?



BJT Transfer Function

BE KVL: $v_i = R_B i_B + v_{BE}$

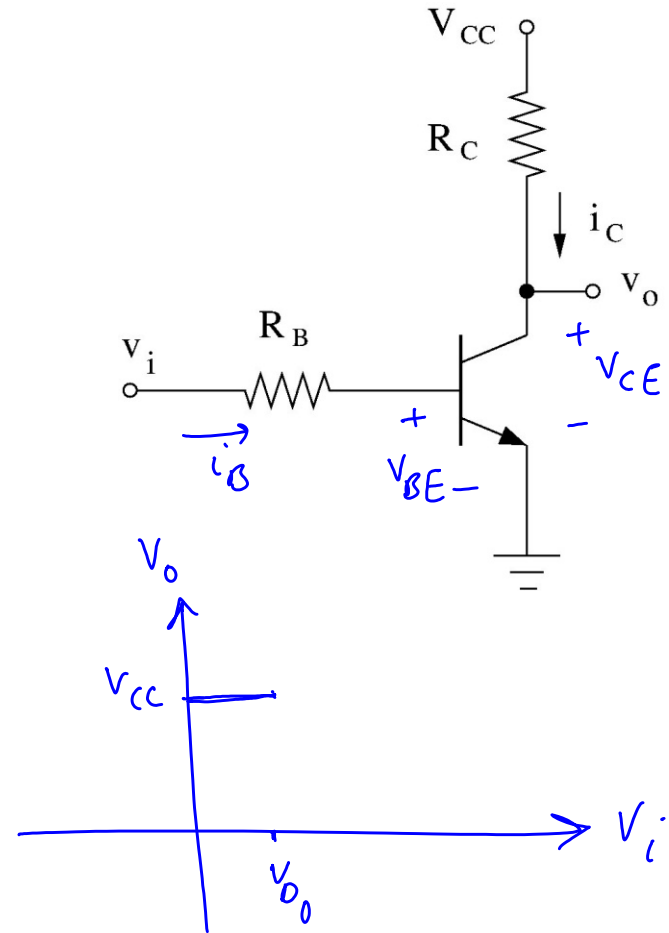
CE KVL: $V_{CC} = R_C i_C + v_{CE}$

Case 1: BJT is in cut-off

$$i_B = 0, v_{BE} < V_{D0}, i_C = 0, i_E = 0$$

$$v_i = v_{BE} < V_{D0} \rightarrow v_i < V_{D0}$$

$$V_{CC} = R_C \times 0 + v_o \rightarrow v_o = V_{CC}$$



For $v_i < V_{D0}$, BJT is in cut-off, $v_o = V_{CC}$

BJT Transfer Function

Case 2: BJT is ON, $V_{DE} = V_{D_0}$

$$i_B = \frac{V_i - V_{BE}}{R_B} = \frac{V_i - V_{D_0}}{R_B},$$

$$V_{CE} = V_{CC} - R_C i_C$$

$$i_C = \beta i_B, \quad V_{CE} \geq V_{D_0}$$

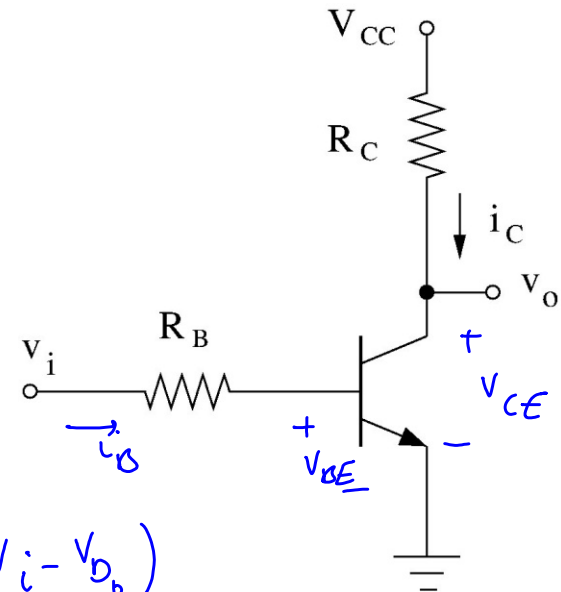
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$$i_C = \frac{\beta}{R_B} (V_i - V_{D_0}), \quad V_{CE} = V_{CC} - \frac{\beta R_C}{R_B} (V_i - V_{D_0})$$

$$V_{CE} \geq V_{D_0} \rightarrow V_i \leq V_{D_0} + \frac{V_{CC} - V_{D_0}}{\beta R_C / R_B}$$

$$V_o = \left(V_{CC} + \frac{\beta R_C}{R_B} V_{D_0} \right) - \frac{\beta R_C}{R_B} V_i$$

For $V_i \leq V_{D_0} + \frac{V_{CC} - V_{D_0}}{\beta R_C / R_B}$ the BJT is in active mode.



BJT Transfer Function

Case 3: BJT is in saturation.

$$V_{BE} = V_{D_0}, \quad \boxed{i_c < \beta i_B}, \quad V_{CE} = V_{sat}$$

$$i_B = \frac{V_i - V_{BE}}{R_B},$$

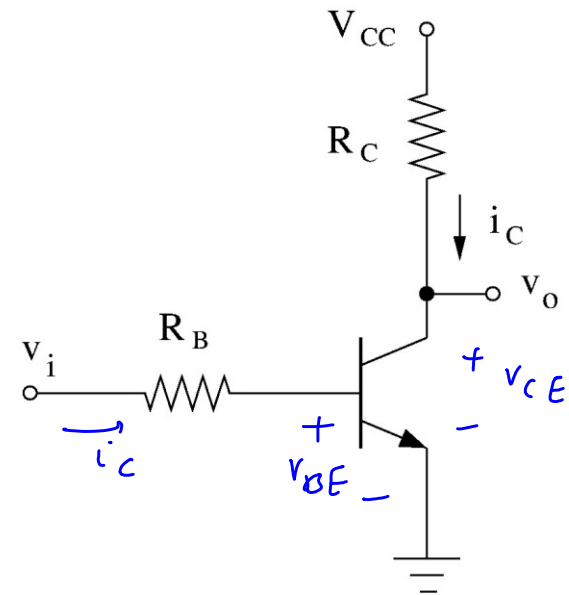
$$V_{CE} = V_{CC} - R_C i_c, \quad i_c = \frac{V_{CC} - V_{sat}}{R_C}$$

$$i_c < \beta i_B \rightarrow \frac{V_{CC} - V_{sat}}{R_C} < \frac{\beta}{R_B} (V_i - V_{D_0})$$

$$V_i > V_{D_0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B}$$

For $V_i > V_{D_0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B}$, BJT is in saturation

$$V_o = V_{sat}$$



BJT Transfer Function

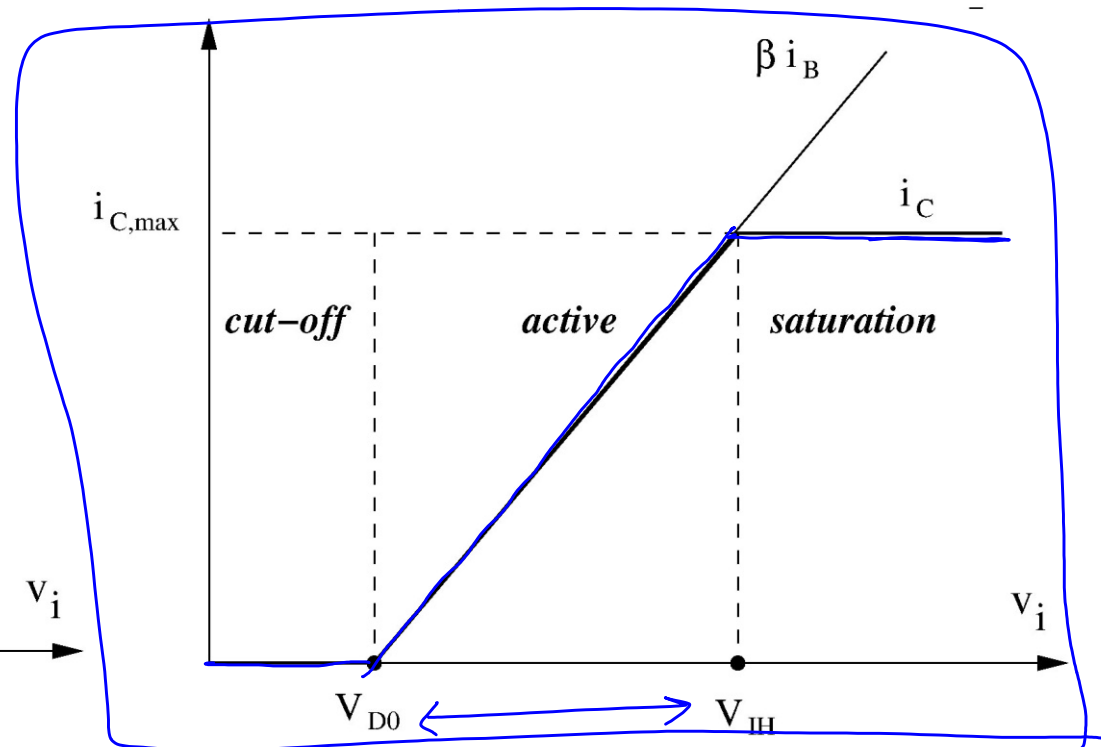
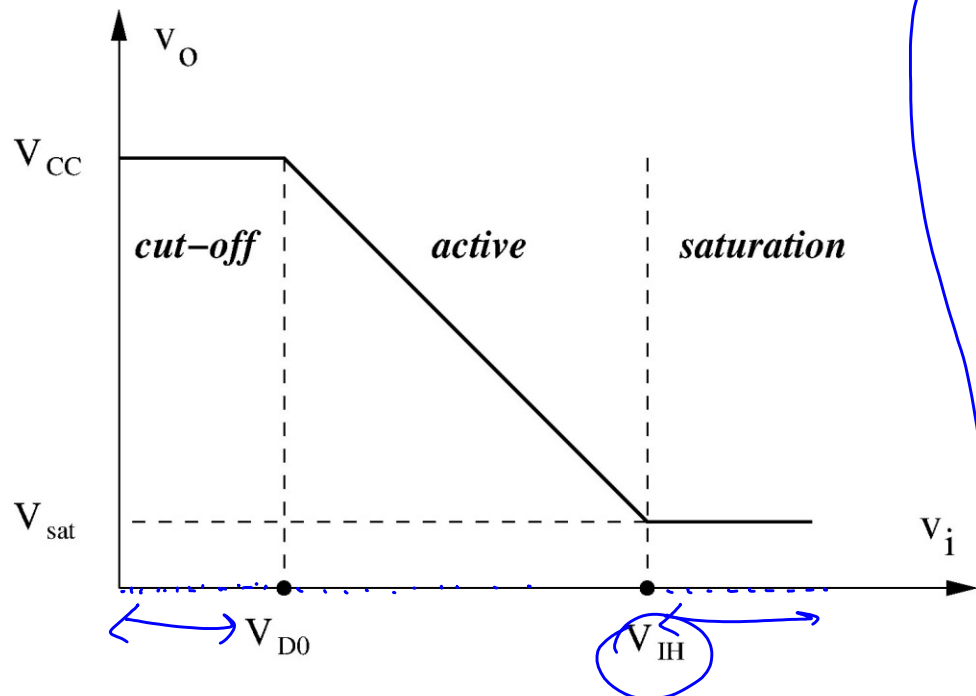
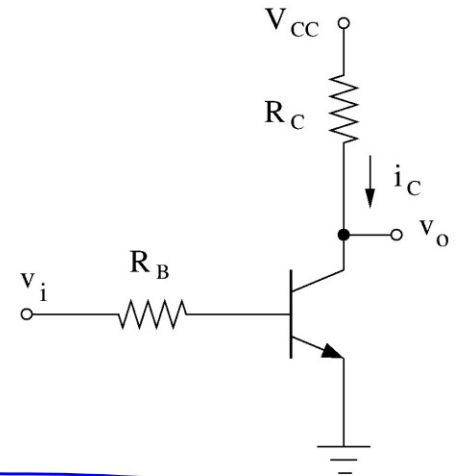
$$v_i < V_{D0}$$

→ BJT in Cutoff

$$V_{D0} \leq v_i \leq V_{D0} + \frac{V_{CC} - V_{D0}}{\beta R_C / R_B} \rightarrow \text{BJT in active}$$

$$V_{D0} + \frac{V_{CC} - V_{sat}}{\beta R_C / R_B} < v_i$$

→ BJT in deep saturation



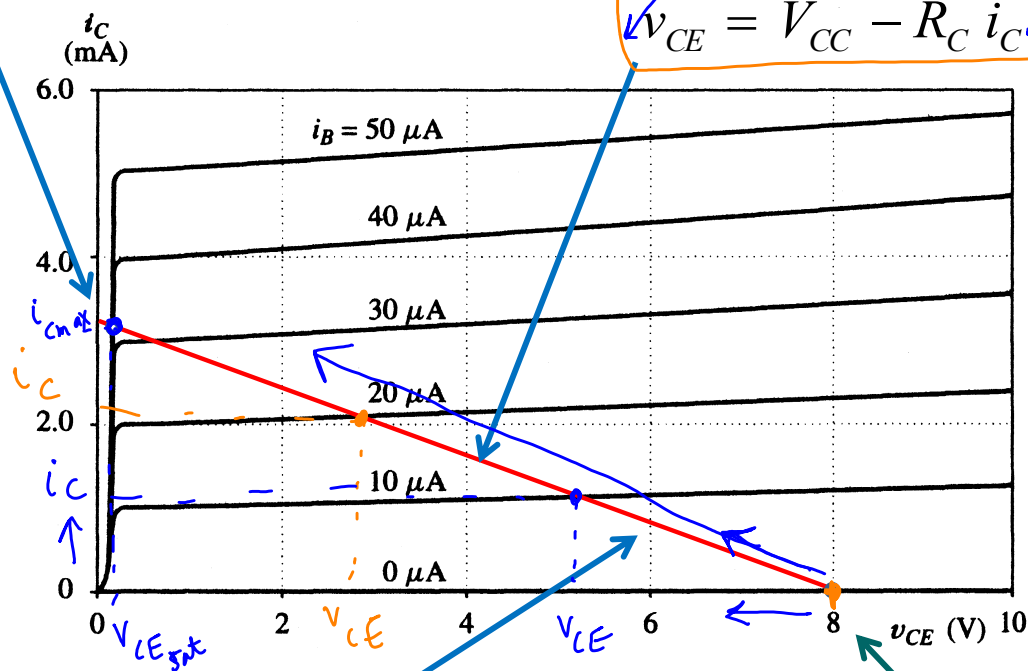
BJT transfer function on the load line

Saturation : $V_{IH} < v_i$

i_B increases but i_C unchanged

Load Line (CE - KVL)

$$v_{CE} = V_{CC} - R_C i_C$$

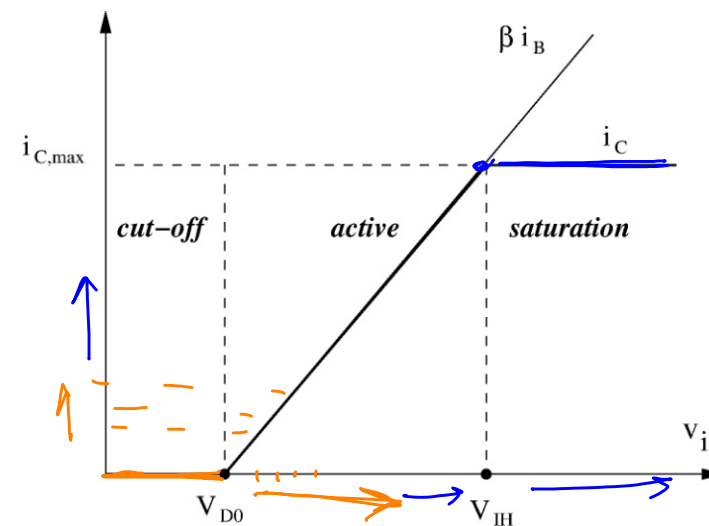
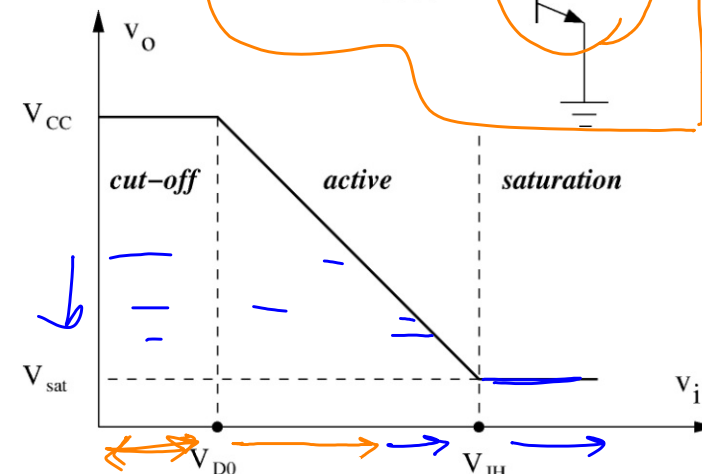
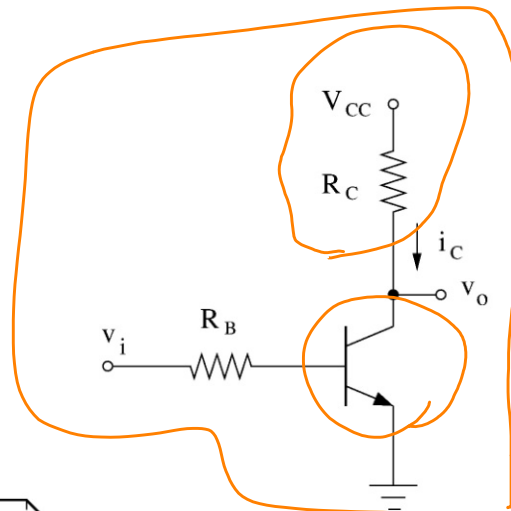


Active : $V_{D0} \leq v_i \leq V_{IH}$

i_B & i_C increase together

Cut - off :

$$v_i < V_{D0}$$



BJT β varies substantially

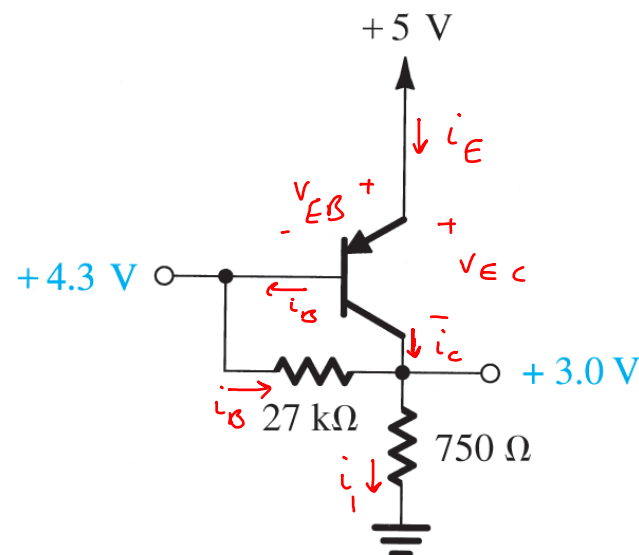
Transistor β depends on many factors:

- Strongly depends on temperature (9% increase per °C)
- Depends on i_C (not constant as assumed in the model)
- β of similarly manufactured BJT can vary (manufacturer spec sheet typically gives a range as well as an average value for β)
- β_{min} is an important parameter. For example, to ensure operation in deep saturation for all similar model BJTs, we need to set $i_C / i_B < \beta_{min}$

Lecture 12 reading quiz

A few measurements on the below circuit produces the labeled voltages.

Find the value of β (Assume $V_{D0} = 0.7V$).



$$V_{EB} = V_E - V_B = 5V - 4.3V = 0.7V \rightarrow \text{BJT is ON}$$

$$V_{EC} = V_E - V_C = 5V - 3V = 2V > 0.7$$

\downarrow
BJT is in active mode

$$\rightarrow i_C = \beta i_B, \quad i_I = i_C + i_B$$

$$i_I = \frac{3V}{750\Omega} = 4mA \Rightarrow i_I = 4mA$$

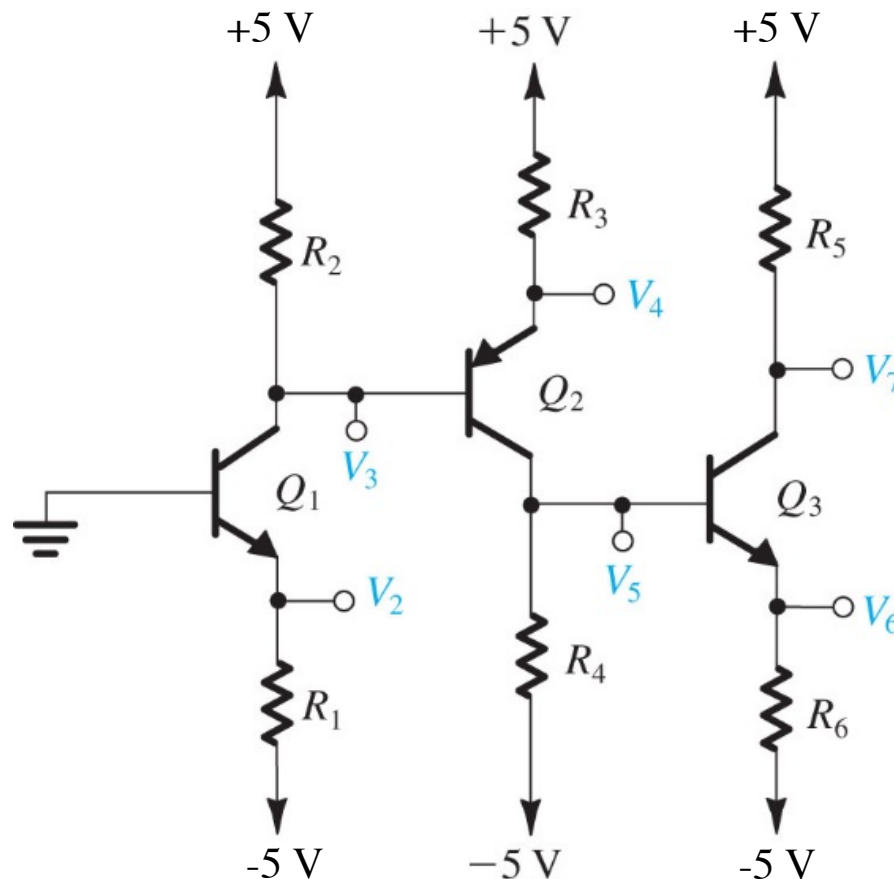
$$i_B = \frac{4.3V - 3V}{27k\Omega} = 48\mu A \Rightarrow i_B = 48\mu A$$

$$i_I = i_B + \beta i_B \Rightarrow i_I = (1 + \beta) i_B \Rightarrow 4mA = (1 + \beta) 48\mu A$$

$$\Rightarrow \beta = 82.3$$

Discussion question 2.

Using $\beta = \infty$, design the following circuit so that the transistors operate in the active region and the collector currents in Q_1 , Q_2 , and Q_3 are 2 mA, 2 mA, and 4 mA, respectively, and $V_3 = 0$, $V_5 = -4$ V, and $V_7 = 2$ V.



$$V_3 = 0V \text{ \& } i_{c_1} = 2mA$$

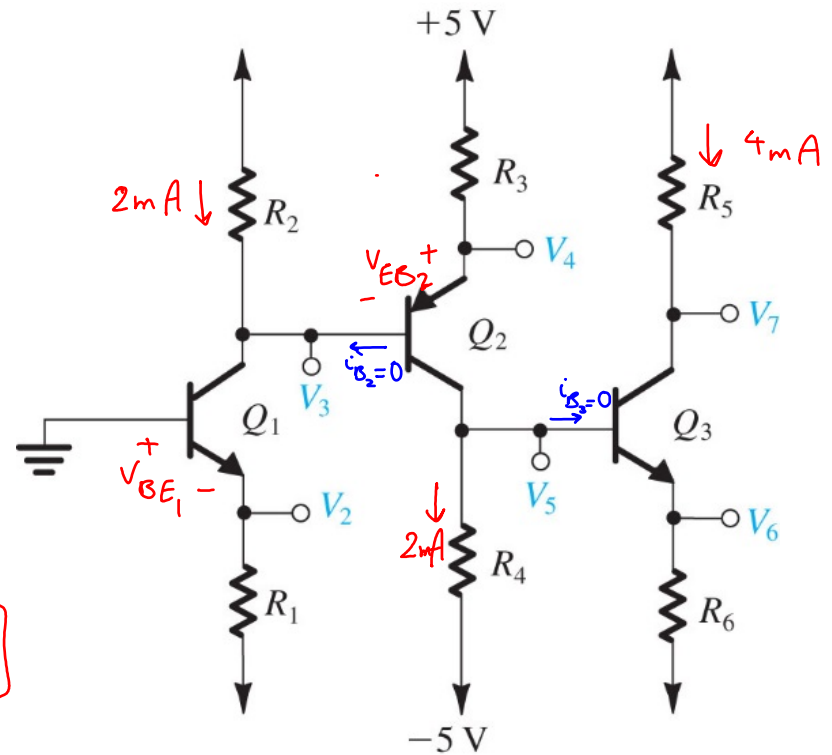
$$\frac{5V - 0V}{R_2} = 2mA \rightarrow R_2 = 2.5k\Omega$$

$$Q_1 \text{ is ON} \rightarrow V_{BE_1} = V_{B_1} - V_{E_1} = 0.7$$

$$\rightarrow V_2 = -0.7V$$

$$\beta = \infty \rightarrow i_{c_1} = i_{E_1} = 2mA$$

$$R_1 = \frac{V_2 - (-5)}{2mA} = \frac{-0.7 + 5}{2mA} \rightarrow R_1 = 2.15k\Omega$$



$$R_4 = \frac{V_5 - (-5V)}{2mA} = \frac{-4V + 5V}{2mA} \rightarrow R_4 = 0.5k\Omega$$

$$Q_2 \text{ is ON} \rightarrow V_{EB_2} = V_{E_2} - V_{B_2} = 0.7V \rightarrow V_4 = 0.7V + 0 \rightarrow V_4 = 0.7V$$

$$\beta = \infty \rightarrow i_{c_2} = i_{E_2} = 2mA$$

$$R_3 = \frac{5V - V_4}{2mA} = \frac{5V - 0.7}{2mA} = \frac{4.3V}{2mA} \rightarrow R_3 = 2.15k\Omega$$

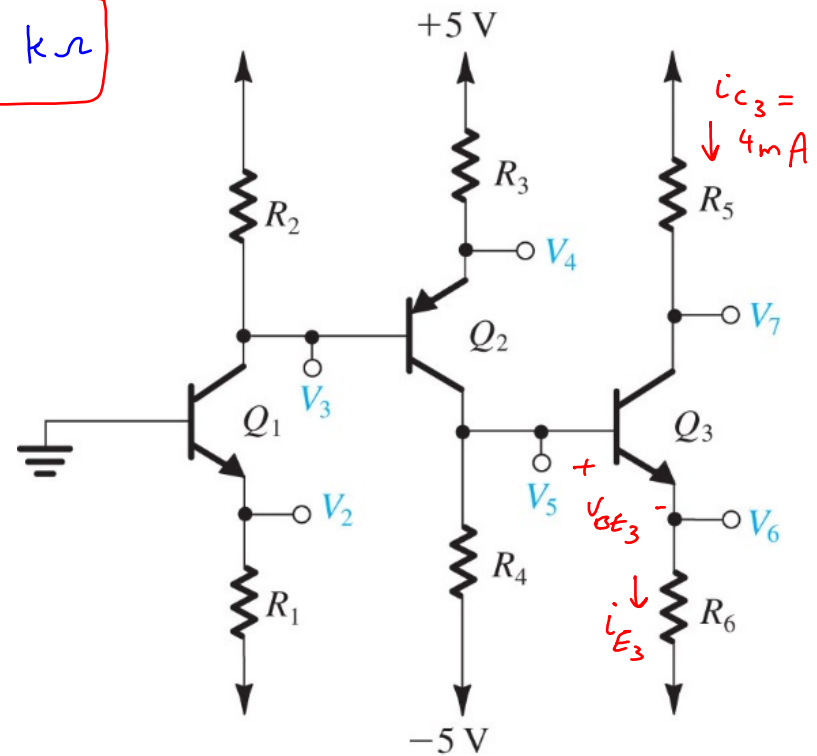
$$R_5 = \frac{5V - V_7}{4mA} = \frac{5V - 2V}{4mA} \rightarrow R_5 = 0.75 k\Omega$$

$$Q_3 \text{ is ON} \rightarrow V_{BE3} = V_5 - V_6 = 0.7V$$

$$\rightarrow V_6 = -4.7V$$

$$\beta = \infty \rightarrow i_{C3} = i_{E3} = 4mA$$

$$R_6 = \frac{-4.7 - (-5)}{4mA} \rightarrow R_6 = 75\Omega$$



Discussion question 2.

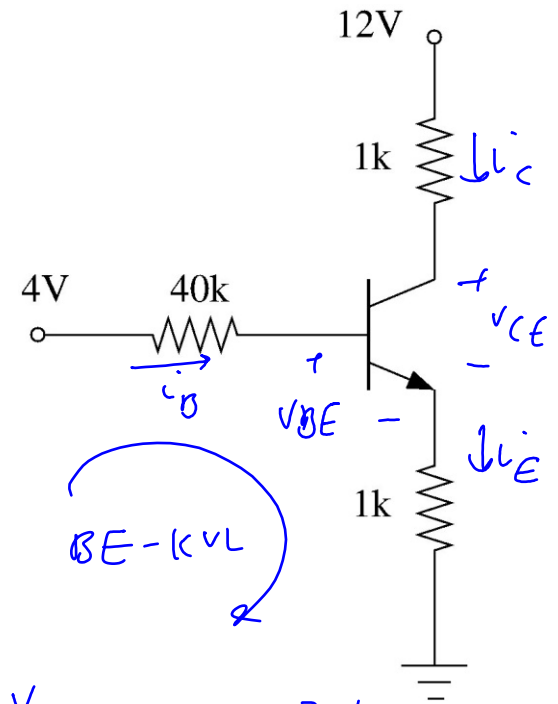
Find the transistor parameters in this BJT circuit. ($\beta = 100$, $V_{D0} = 0.7V$, $V_{sat} = 0.2V$).

Assume BJT is in cut off, $i_B = 0$, $i_C = 0$, $i_E = 0$
 $V_{BE} < 0.7V$

BE-KVL:

$$4V = 40k \times i_B + V_{BE} + 1k \times i_E$$

if $i_B = i_E = 0 \rightarrow V_{BE} = 4V > 0.7 \rightarrow$ BJT is ON



Assume BJT is in active mode: $i_C = \beta i_B$, $V_{CE} \geq V_{D0}$, $V_{BE} = 0.7V$

$$i_E = i_C + i_B \rightarrow i_E = (1 + \beta) i_B$$

$$4V = 40k \times i_B + 0.7 + 1k (101) i_B$$

$$i_B = 23.4 \mu A, \quad i_E = 2.36 mA, \quad i_C = 2.34 mA$$

CE KVL:

$$12V = 1k \times i_C + V_{CE} + 1k \times i_E$$

$$12V = 1k \times 2.34mA + V_{CE} + 1k \times 2.36mA$$

$$\rightarrow V_{CE} = 7.3V > 0.7V$$

BJT is in active mode.

